

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L8	0	"PG-PUBS INTERFERENCE SEARCH"	US-PGPUB; USPAT	OR	ON	2008/12/08 09:40
L7	1	(method process procedure) and etch \$4 and plasma and (layer film) and organic and (Si silicon) and (containing comprising) and (organic mask\$4) and ((NH3 "NH.sub.3" ammonia) and (O2 "O.sub.2" oxygen)) and CD and control\$4 and flow and ratio and electrode and residence adj time and volume and exhaust adj velocity and capacitively adj coupled and (distance spacing gap) and electrode	US-PGPUB; USPAT	OR	ON	2008/12/08 09:39
L6	1	(method process procedure) and etch \$4 and plasma and (layer film) and organic and (Si silicon) and (containing comprising) and (organic mask\$4) and ((NH3 "NH.sub.3" ammonia) and (O2 "O.sub.2" oxygen)) and CD adj shift and control\$4 and flow and ratio and electrode and residence adj time	US-PGPUB; USPAT	OR	ON	2008/12/08 09:38

		and volume and exhaust adj velocity and capacitively adj coupled and (distance spacing gap) and electrode				
L5	1	(method process procedure) and etch \$4 and plasma and (layer film) same organic and (Si silicon) same (containing comprising) same (organic mask\$4) and ((NH3 "NH.sub.3" ammonia) and (O2 "O.sub.2" oxygen)) and CD adj shift and control\$4 and flow and ratio and electrode and residence adj time and volume and exhaust adj velocity and capacitively adj coupled and (distance spacing gap) same electrode	US-PGPUB; USPAT	OR	ON	2008/12/08 09:38
L4	1	(method process procedure) and etch \$4 and plasma and (layer film) with organic and (Si silicon) with (containing comprising) with (organic mask\$4) and ((NH3 "NH.sub.3" ammonia) and (O2 "O.sub.2" oxygen)) and CD adj shift and control\$4 and flow and ratio and electrode and residence adj time and volume and exhaust adj velocity	US-PGPUB; USPAT	OR	ON	2008/12/08 09:37

		and capacitively adj coupled and (distance spacing gap) with electrode				
L3	0	(method process procedure) and etch \$4 and plasma and (layer film) with organic and (Si silicon) with (containing comprising) with (organic mask\$4) and ((NH3 "NH.sub.3" ammonia) and (O2 "O.sub.2" oxygen)) and CD adj shift and control\$4 and flow and ratio and electrode and residence adj time and volume and exhaust adj velocity and capacitively adj coupled and (distance spacing gap) near electrode	US-PGPUB; USPAT	OR	ON	2008/12/08 09:37
L2	0	(method process procedure) and etch \$4 and plasma and (layer film) near organic and (Si silicon) with (containing comprising) with (organic mask\$4) and ((NH3 "NH.sub.3" ammonia) and (O2 "O.sub.2" oxygen)) and CD adj shift and control\$4 and flow and ratio and electrode and residence adj time and volume and exhaust adj velocity and capacitively adj coupled and (distance	US-PGPUB; USPAT	OR	ON	2008/12/08 09:37

		spacing gap) near electrode				
L1	0	(method process procedure) and etch \$4 and plasma and (layer film) near organic and (Si silicon) near2 (containing comprising) near2 (organic mask\$4) and ((NH3 "NH.sub.3" ammonia) and (O2 "O.sub.2" oxygen)) and CD adj shift and control\$4 and flow and ratio and electrode and residence adj time and volume and exhaust adj velocity and capacitively adj coupled and (distance spacing gap) near electrode	US-PGPUB; USPAT	OR	ON	2008/12/08 09:35

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